

10/565624**AP20 Rec'd PCT/PTO 24 JAN 2006****IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re U.S. Patent Application of)
 SUDA et al.)
 Application Number: To Be Assigned)
 Filed: Concurrently Herewith)
 For: FIELD EFFECT TRANSISTOR AND METHOD FOR)
 MANUFACTURING SAME)
 ATTORNEY DOCKET NO. HIRA.0217)

Honorable Assistant Commissioner
 for Patents
 Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Pursuant to 37 C.F.R. §§ 1.56 and 1.97, this Information Disclosure Statement is submitted in the above-identified National Stage U.S. patent application. A listing of documents to be published on the face of any patent granted from this application is submitted herewith on Form PTO-1449. Any other documents or information submitted for consideration by the Examiner are listed in this paper. A copy of each foreign patent, or each publication or portion thereof listed or herein identified, is submitted herewith.

CERTIFICATION

This Information Disclosure Statement is submitted with the initial filing of the application. Accordingly, no fee is due or payable at this time.

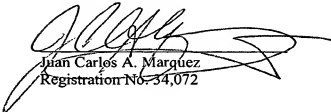
The Examiner is requested to acknowledge consideration of the information provided in this paper in accordance with prescribed procedures.

10/565624**LAP 20 Rec'd PCT/PTO 24 JAN 2006**

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U.S. Department of Commerce Patent and Trademark Office	APPLICANT SUDA et al.	
Information Disclosure Statement by Applicant	FILING DATE Concurrently Herewith	GROUP

U.S. Patent Documents

Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	5,900,648	5/4/99	Harris et al.			3/28/97

Foreign Patent Documents

Examiner Initial	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
						Yes	No
	2000-150792	11/11/98	Japan			Abstract	X
	2001-094099	9/21/99	Japan			Abstract	X
	2002-246594	12/21/2001	Japan			Abstract	X
	FR 2 707 425	7/9/93	France			Abstract	X

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

	International Search Report of PCT/JP2004/010696 mailed November 9, 2004
	James Kolodzey et al., "Electrical Conduction and Dielectric Breakdown in Aluminum Oxide Insulators on Silicon", IEEE Transactions on Electron Devices, Vol. 47, No. 1, January 2000, pp. 121-128
	N. Onojima et al., "Heteroepitaxial Growth of Insulating AlN on 6H-SiC by MBE", Materials Science Forum Vols. 389-393, (2002), pp. 1457-1460
	N. Onojima et al., "Impact of SiC Surface Control on Initial Growth Mode and Crystalline Quality of AlN Grown by Molecular-Beam Epitaxy", 5 th International Conference on Nitride Semiconductors, May 25-30, 2003, Technical Digest, pp. 28 and 228
	N. Onojima et al., "Lattice Relaxation Process of AlN Growth on Atomically Flat 6H-SiC Substrate in Molecular Beam Epitaxy", Journal of Crystal Growth (2002), pp. 1012-1016
	N. Onojima et al., "Molecular-Beam Epitaxial Growth of Insulating AlN on Surface-Controlled 6H-SiC Substrate by HCl Gas Etching", Applied Physics Letters, Vol. 80, No. 1, January 7, 2002, pp. 76-78
	Jun Suda et al., "Effects of 6H-SiC Surface Reconstruction on Lattice Relaxation of AlN Buffer Layers in Molecular-Beam Epitaxial Growth of GaN", Applied Physics Letters, Vol. 81, No. 27, December 30, 2002, pp. 5141-5143
	N. Onojima et al., "Impact of SiC Surface control on Initial Growth Mode and Crystalline Quality of AlN Grown by Molecular-Beam Epitaxy", Phys. Stat. Sol. No. 7 (2003), pp. 2529-2532
	N. Onojima et al., "High-Quality AlN by Initial Layer-by-Layer Growth on Surface-Controlled 4H-SiC(0001) Substrate", Jpn. J. Appl. Phys., Vol. 42 (May 1, 2003), pp. L445-L447

EXAMINER /Selim Ahmed/

DATE CONSIDERED 12/22/2008

EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

PTO1449

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /S.A./